

# NTD4808N, NVD4808N

## MOSFET – Power, Single, N-Channel, DPAK/IPAK 30 V, 63 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

### Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

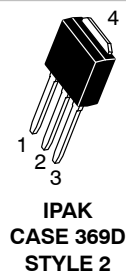
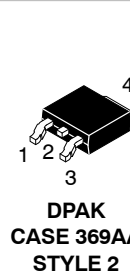
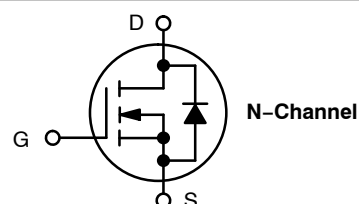
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	30	V
Gate-to-Source Voltage			V <sub>GS</sub>	±20	V
Continuous Drain Current R <sub>θJA</sub> (Note 1)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	13.8	A
		T <sub>A</sub> = 85°C		10.7	
Power Dissipation R <sub>θJA</sub> (Note 1)		T <sub>A</sub> = 25°C	P <sub>D</sub>	2.63	W
Continuous Drain Current R <sub>θJA</sub> (Note 2)		T <sub>A</sub> = 25°C	I <sub>D</sub>	10	A
		T <sub>A</sub> = 85°C		7.8	
Power Dissipation R <sub>θJA</sub> (Note 2)		T <sub>A</sub> = 25°C	P <sub>D</sub>	1.4	W
Continuous Drain Current R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 25°C	I <sub>D</sub>	63	A
		T <sub>C</sub> = 85°C		49	
Power Dissipation R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 25°C	P <sub>D</sub>	54.6	W
Pulsed Drain Current	t <sub>p</sub> =10μs	T <sub>A</sub> = 25°C	I <sub>DM</sub>	126	A
Current Limited by Package		T <sub>A</sub> = 25°C	I <sub>DmaxPkg</sub>	45	A
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>STG</sub>	–55 to +175	°C
Source Current (Body Diode)			I <sub>S</sub>	45	A
Drain to Source dV/dt			dV/dt	6	V/ns



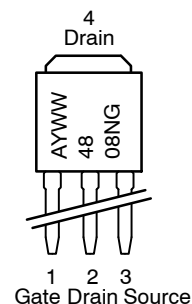
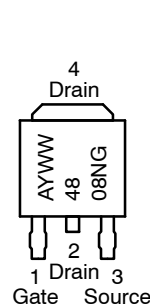
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	8.0 m $\Omega$ @ 10 V	63 A
	12.4 m $\Omega$ @ 4.5 V	



### MARKING DIAGRAMS & PIN ASSIGNMENTS



A = Assembly Location\*  
Y = Year  
WW = Work Week  
4808N = Device Code  
G = Pb-Free Package

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# NTD4808N, NVD4808N

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain-to-Source Avalanche Energy (V <sub>DD</sub> = 24 V, V <sub>GS</sub> = 10 V, I <sub>L</sub> = 17 A <sub>pk</sub> , L = 1.0 mH, R <sub>G</sub> = 25 Ω)	EAS	144.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	R <sub>θJC</sub>	2.75	°C/W
Junction-to-TAB (Drain)	R <sub>θJC-TAB</sub>	3.5	
Junction-to-Ambient – Steady State (Note 1)	R <sub>θJA</sub>	57	
Junction-to-Ambient – Steady State (Note 2)	R <sub>θJA</sub>	107	

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			27		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V	T <sub>J</sub> = 25 °C		1	μA
			T <sub>J</sub> = 125°C		10	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.5		2.5	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			5.6		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 to 11.5 V	I <sub>D</sub> = 30 A	6.7	8.0	mΩ
			I <sub>D</sub> = 15 A	6.6		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 30 A	10.3	12.4	
			I <sub>D</sub> = 15 A	9.8		
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		11.4		S

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 12 V		1538		pF
Output Capacitance	C <sub>OSS</sub>			334		
Reverse Transfer Capacitance	C <sub>RSS</sub>			180		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

# NTD4808N, NVD4808N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>CHARGES AND CAPACITANCES</b>						
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		11.3	13	nC
Threshold Gate Charge	$Q_{G(TH)}$			1.6		
Gate-to-Source Charge	$Q_{GS}$			4.9		
Gate-to-Drain Charge	$Q_{GD}$			4.9		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		26		nC

## SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		12.3		ns
Rise Time	$t_r$			21.3		
Turn-Off Delay Time	$t_{d(OFF)}$			14.6		
Fall Time	$t_f$			6.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		7.7		ns
Rise Time	$t_r$			19.5		
Turn-Off Delay Time	$t_{d(OFF)}$			23		
Fall Time	$t_f$			3.5		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.93	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.83		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$			20		ns
Charge Time	$t_a$				10.4		
Discharge Time	$t_b$				9.6		
Reverse Recovery Charge	$Q_{RR}$				9.7		nC

## PACKAGE PARASITIC VALUES

Source Inductance	$L_S$	$T_A = 25^\circ\text{C}$		2.49		nH
Drain Inductance, DPAK	$L_D$			0.0164		
Drain Inductance, IPAK	$L_D$			1.88		
Gate Inductance	$L_G$			3.46		
Gate Resistance	$R_G$			1.1		$\Omega$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

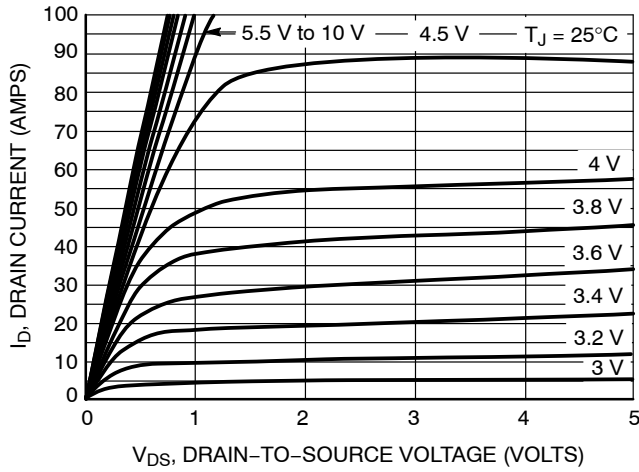


Figure 1. On-Region Characteristics

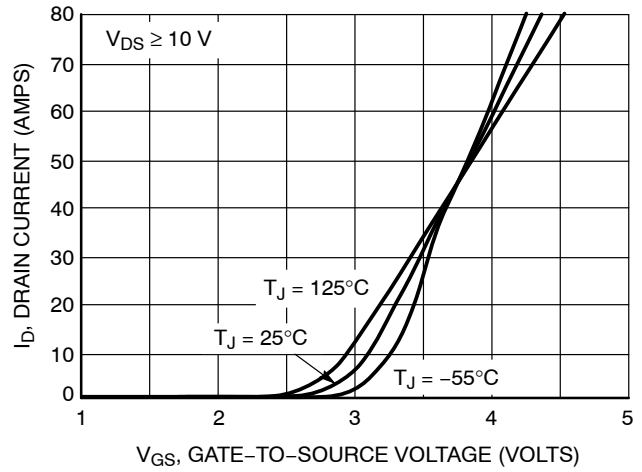


Figure 2. Transfer Characteristics

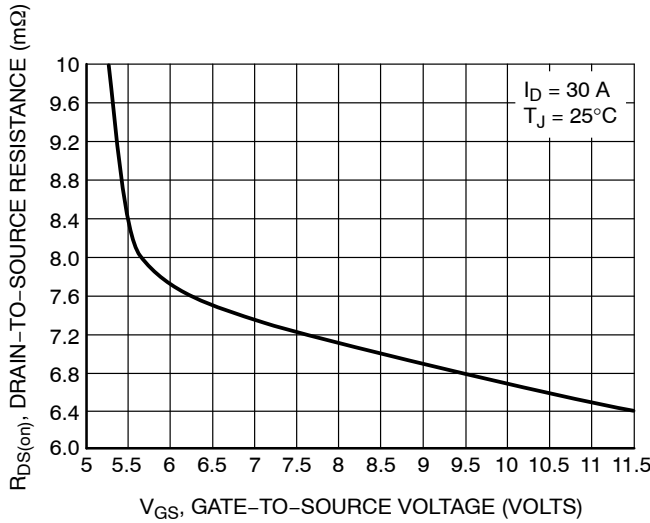


Figure 3. On-Resistance vs. Gate-to-Source Voltage

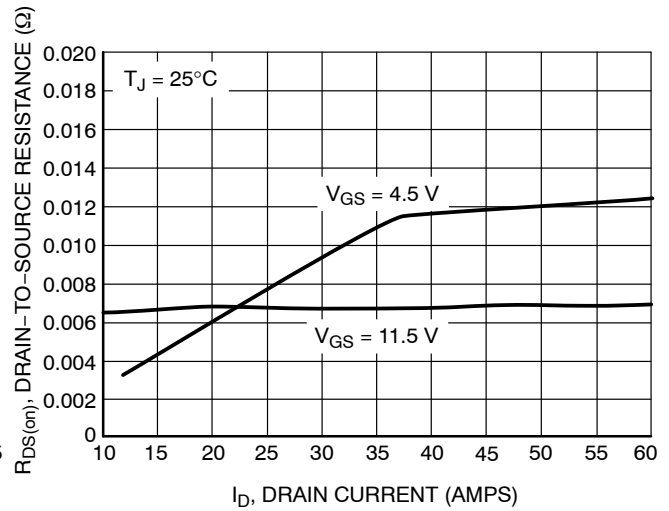


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

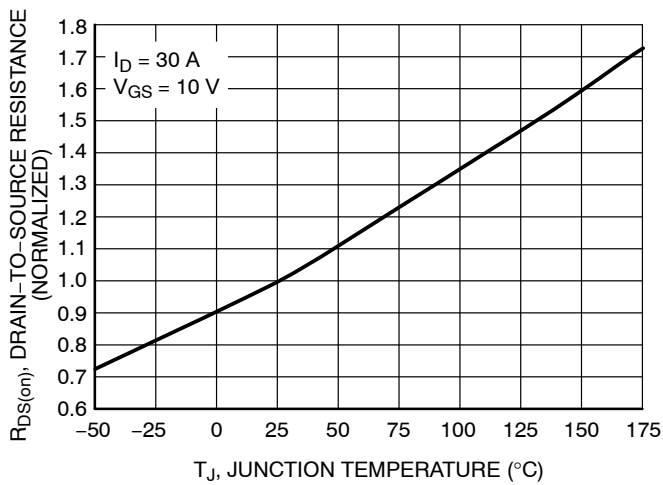


Figure 5. On-Resistance Variation with Temperature

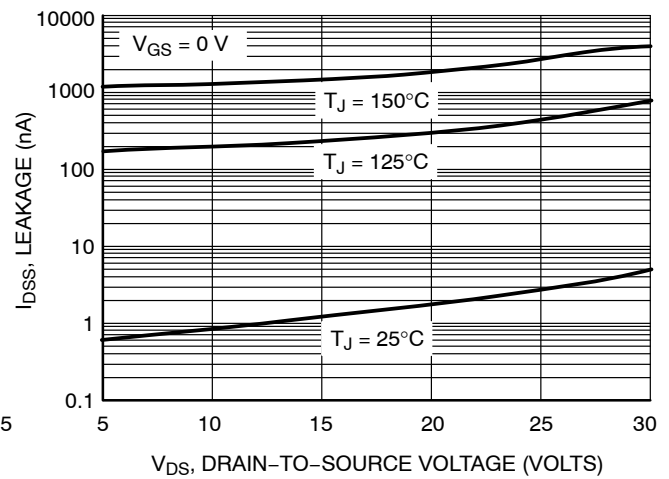


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

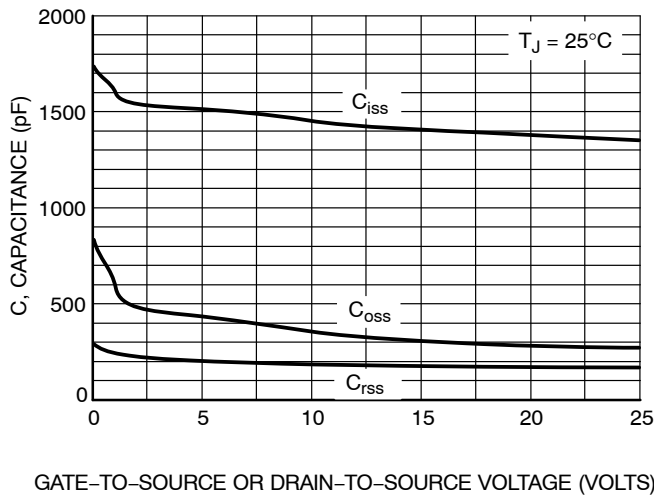


Figure 7. Capacitance Variation

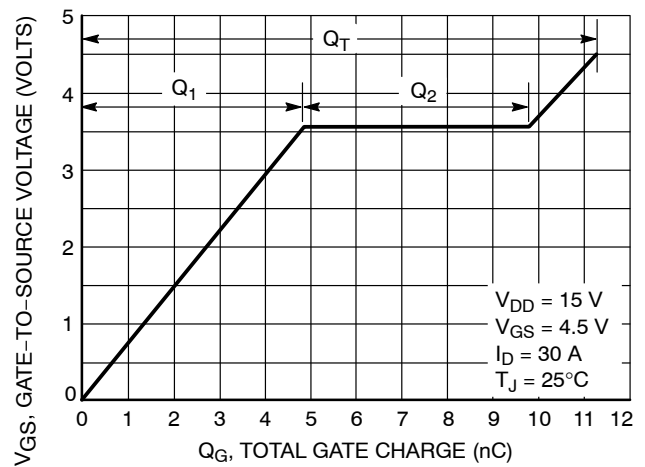


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

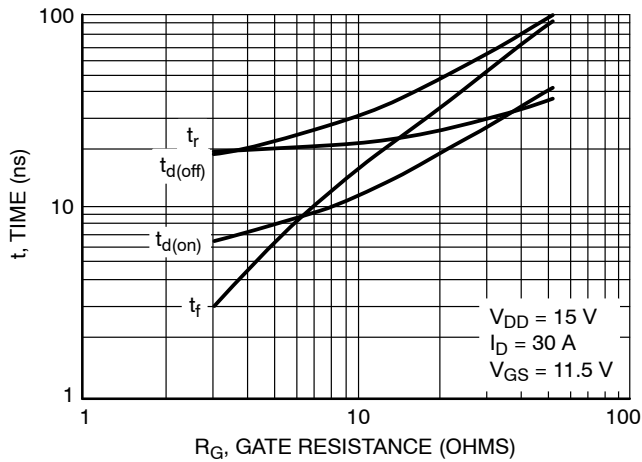


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

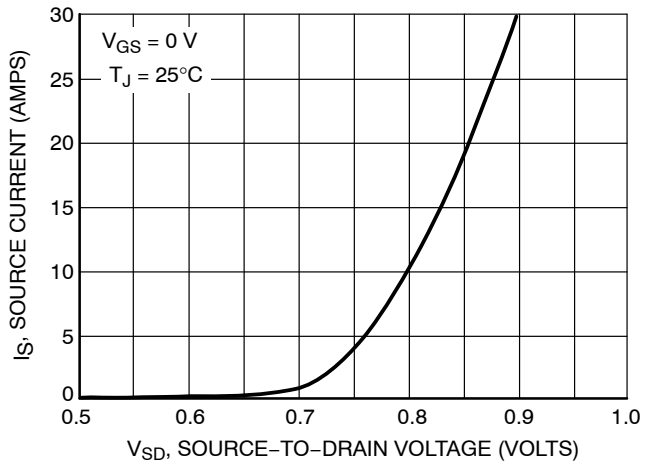


Figure 10. Diode Forward Voltage vs. Current

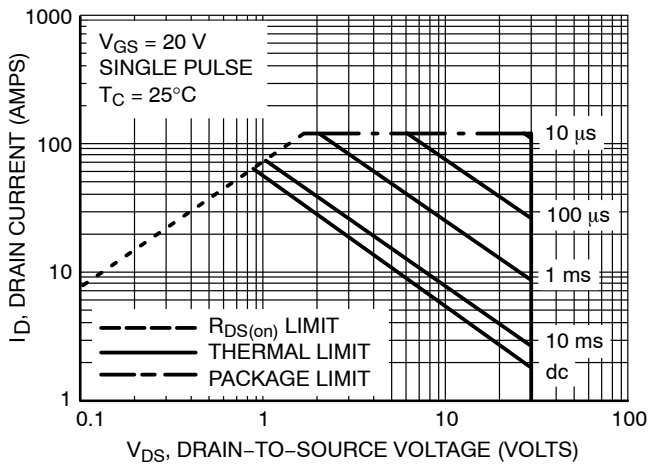


Figure 11. Maximum Rated Forward Biased Safe Operating Area

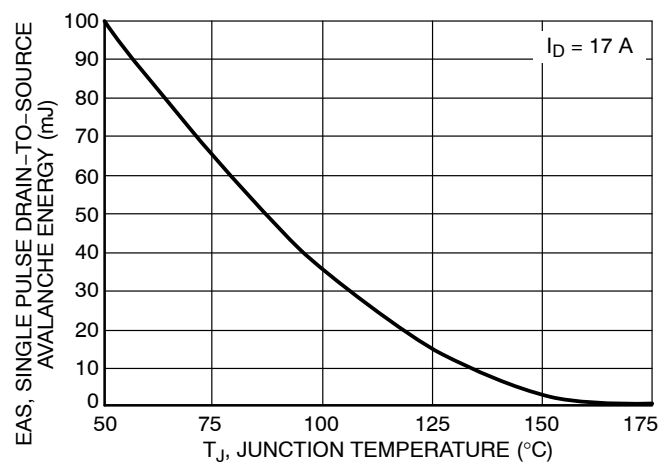


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

# NTD4808N, NVD4808N

## TYPICAL PERFORMANCE CURVES

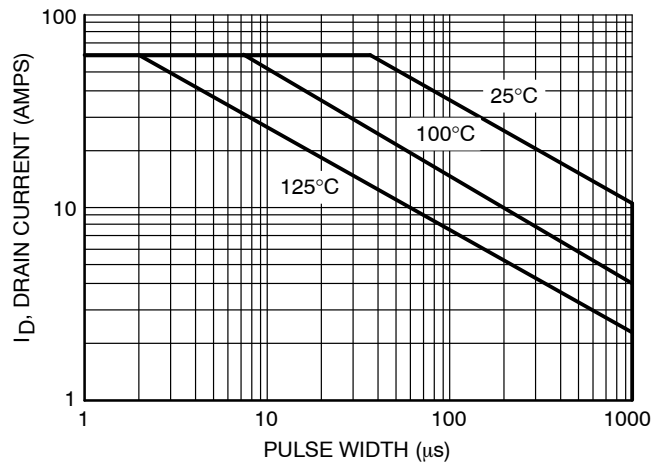


Figure 13. Avalanche Characteristics

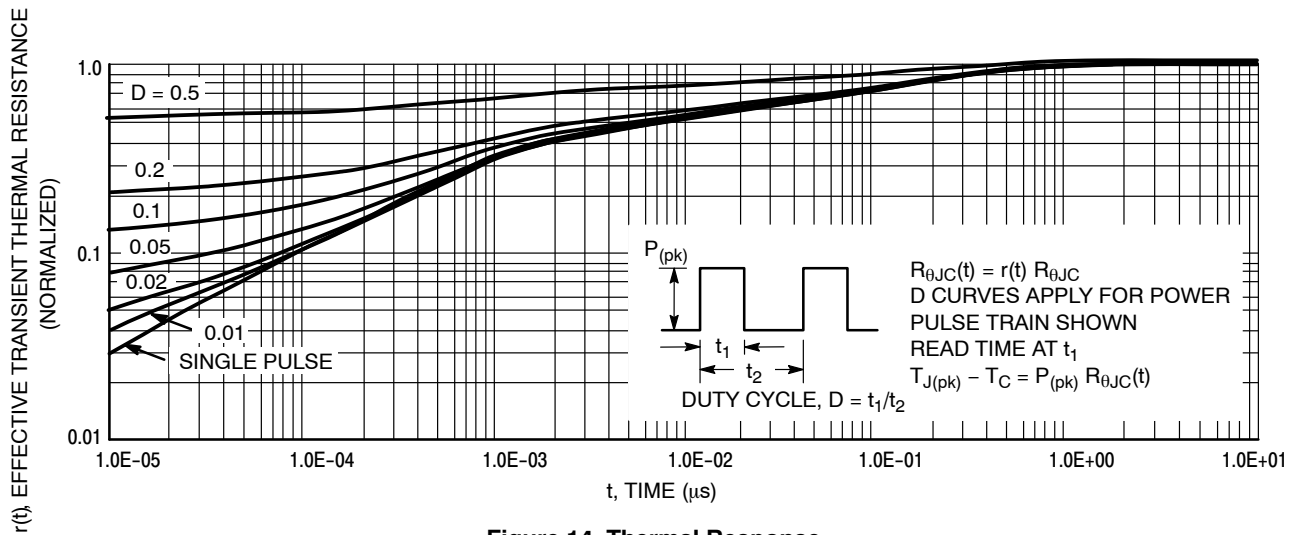


Figure 14. Thermal Response

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTD4808NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD4808N-1G	IPAK (Pb-Free)	75 Units / Rail
NVD4808NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

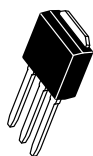
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

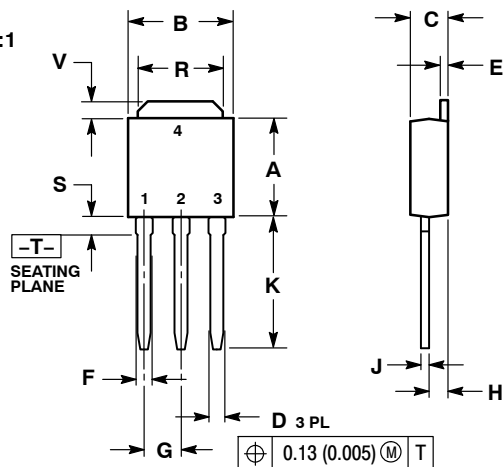
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DATE 15 DEC 2010

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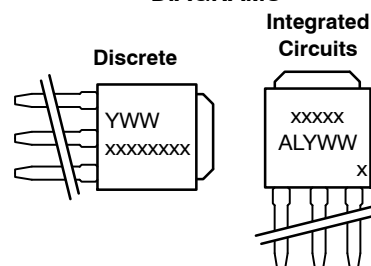


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

### MARKING DIAGRAMS

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN
- STYLE 3:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE
- STYLE 4:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE
- STYLE 5:  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE
- STYLE 6:  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2
- STYLE 7:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR



xxxxxxxx = Device Code  
A = Assembly Location  
IL = Wafer Lot  
Y = Year  
WW = Work Week

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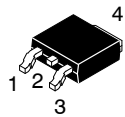
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# MECHANICAL CASE OUTLINE

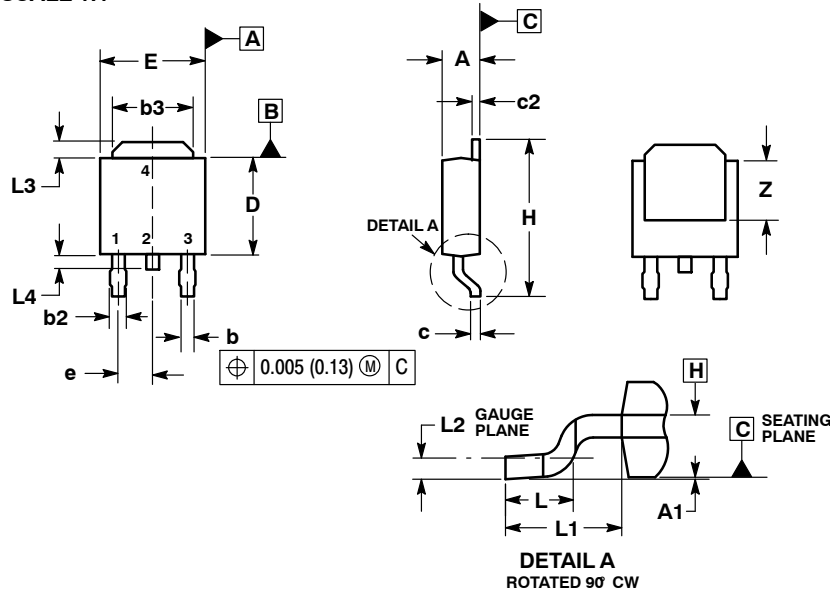
## PACKAGE DIMENSIONS

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SCALE 1:1



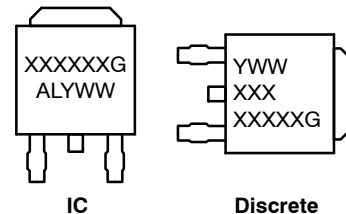
### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	0.040	0.040	1.01	1.01
Z	0.155		3.93	

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN
- STYLE 3:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE
- STYLE 4:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE
- STYLE 5:  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE
- STYLE 6:  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2
- STYLE 7:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

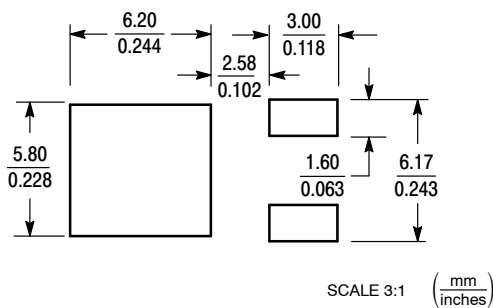
### GENERIC MARKING DIAGRAM\*



- XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

### SOLDERING FOOTPRINT\*




\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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